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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/601,958	06/23/2003	Chun-Yi Yang	MXIC-P910252 8883	
7	590 08/27/2004		EXAMINER	
Kenton R. Mullins			HA, NATHAN W	
Stout, Uxa, Buyan & Mullins, LLP				DADED MAKEE
Suite 300			ART UNIT	PAPER NUMBER
4 Venture Irvine, CA 92618			2814 DATE MAILED: 08/27/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	_
	10/601,958	YANG, CHUN-YI	
Office Action Summary	Examiner	Art Unit	_
	Nathan W. Ha	2814	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be t y within the statutory minimum of thirty (30) da will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDON	mely filed ys will be considered timely. the mailing date of this communication. ED (35 U.S.C. § 133).	
Status		1 ,	
1) Responsive to communication(s) filed on 15 J	une 2004.		
	s action is non-final.		
Since this application is in condition for allowa closed in accordance with the practice under the second sec	nce except for formal matters, pr		
Disposition of Claims			
 4) ☐ Claim(s) 1-19 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) ☐ Claim(s) 17-19 is/are allowed. 6) ☐ Claim(s) 1-16 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or 	wn from consideration.		
Application Papers			
9)☐ The specification is objected to by the Examine	er.		
10)☐ The drawing(s) filed on is/are: a)☐ acc	epted or b) objected to by the	Examiner.	
Applicant may not request that any objection to the			
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex			
Priority under 35 U.S.C. § 119		,	
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Burea * See the attached detailed Office action for a list	ts have been received. ts have been received in Applica rity documents have been receiv u (PCT Rule 17.2(a)).	tion No red in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summar Paper No(s)/Mail I 5) Notice of Informal 6) Other:		

Application/Control Number: 10/601,958

Art Unit: 2814

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

2. Claims 1-3 are rejected under 35 U.S.C. 102(e) as being anticipated by Kim (US 2002/0033495, newly cited.)

In regard to claim 1, in figs. 1-5, Kim, discloses a method of programming memory cells of a memory device, the method comprising:

selectively depositing a first insulating layer 112 over a first portion of the memory cells, region P/C, while not depositing the first insulating layer over a second portion of the memory cells, fig.1; and

selectively depositing a second isolating layers 150 over the second portion of the memory cells, region C, while not depositing the second insulating layers over first portion of the memory cells, to thereby program the memory device.

In regard to claim 2, wherein the first and second portions comprise at least one of electrodes, channels and gate electrodes 108 and 142, fig. 7.

In regard to claim 3, the insulating layer functions as a photoresist layer.

Application/Control Number: 10/601,958 Page 3

Art Unit: 2814

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 4-10 and 12-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kim as applied to claims 1-3 above, and further in view of Wen, US 5,812,448, previously cited.

In regard to claim 4, 6, and 12-13, Kim discloses all of the claimed limitations as mentioned above except step of removing insulating layer to form conductive layer to contact the first portions. It should be noted that conductive layer is normally used to make contacts from the gate to other devices, for example, among gates. For instance, Wen, in fig. 4D, discloses a memory device including removing the insulating layer 32 to form a conductive layer 34 to contact the gate 24' in order to create a word line. This connection is common in memory device since word lines are used to transfer data to and from gates.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention was made to commonly form word lines that make contacts to the gates in order to deliver data to and from gates.

In regard to claims 5 and 16, the cells are transistors; and conductive later contact the first portion. See Kubo's fig. 4D.

Application/Control Number: 10/601,958

Art Unit: 2814

In regard to claim 7, the masking of the predetermined ones of the plurality of memory cells is followed my unmasking the predetermined ones. See Wen's figs. 4C-4D.

In regard to claim 8, the insulating layers are disposed between memory cells. See Wen's fig. 4D.

In regard to claim 9, Kim and Wen further disclose the cells comprise transistors having source/drain regions, gates and word line therein. See Wen's fig.4D.

In regard to claim 10, the cells should have same threshold voltage since they are connecting to the same word line.

In regard to claims 14-15, wherein the first portion is disable. See fig. 4D of Wen.

5. Claim 11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kim and Wen as applied to claims 1-10 and 12-16 above, and further in view of Li et al. US 2003/0228717, previously cited, hereinafter, Li.

In regard to claim 11, Kin and Wen disclose all of the claimed limitations as mentioned above accept the cells are not formed by ion-implantation. It should be noted that deposition is also a well known method of forming active regions deposition provides receiving an indication of a desired constituent ratio and calculating a deposition rate. For instance, Li discloses an analogous device using deposition to form a nonvolatile memory cells. See col. 2, section [0018].

Therefore, it would have been obvious to one of ordinary skilled in the art at the time of the invention was made to obtain well known deposition process to form a

Art Unit: 2814

memory device since it provides receiving an indication of a desired constituent ratio and calculating a deposition rate.

Allowable Subject Matter

6. Claims 17-19 are allowed.

Response to Arguments

7. Applicant's arguments with respect to claims 1-16 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

5. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Art Unit: 2814

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Nathan W. Ha whose telephone number is (571) 272-1707. The examiner can normally be reached on M-TH 8:00-7:00(EST).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Nathan Ha August 23, 2004 ONG PHAM PRIMARY EXAMINER